

SEMICONDUCTOR®

# KA1L0880B/KA1M0880B Fairchild Power Switch(FPS)

#### Features

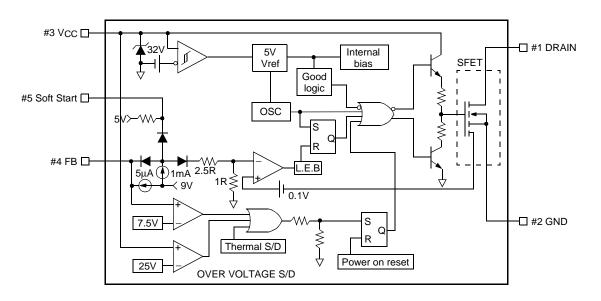
- Precision fixed operating frequency
- KA1L0880B(50KHz),KA1M0880B(67KHz)
- Pulse by pulse over current limiting
- Over load protection
- Over voltage protection (Min. 23V)
- Internal thermal shutdown function
- Under voltage lockout
- Internal high voltage sense FET
- Latch up mode
- Soft start

### Description

The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/ turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit. compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a forward converter.



## Internal Block Diagram



# **Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit	
Maximum Drain voltage <sup>(1)</sup>	V <sub>D,Max</sub>	800	V	
Drain-Gate voltage (R <sub>GS</sub> =1M $\Omega$ )	Vdgr	800	V	
Gate-source (GND) voltage	VGS	±30	V	
Drain current pulsed <sup>(2)</sup>	IDM	32.0	ADC	
Single pulsed avalanche energy <sup>(3)</sup>	EAS	810	mJ	
Avalanche current <sup>(4)</sup>	IAS	15	А	
Continuous drain current (Tc=25°C)	ID	8.0	ADC	
Continuous drain current (T <sub>C</sub> =100°C)	ID	5.6	ADC	
Maximum Supply voltage	VCC,MAX	30	V	
Input voltage range	VFB	-0.3 to V <sub>SD</sub>	V	
Total power dissipation	PD	190	W	
	Derating	1.54	W/°C	
Operating ambient temperature	TA	-25 to +85	°C	
Storage temperature	TSTG	-55 to +150	°C	

Notes:

1. Tj=25°C to 150°C

2. Repetitive rating: Pulse width limited by maximum junction temperature

3. L=24mH, VDD=50V, RG=25 $\Omega$ , starting Tj=25°C

4. L=13 $\mu$ H, starting Tj=25°C

# **Electrical Characteristics (SFET part)**

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Drain source breakdown voltage	BVDSS	VGS=0V, ID=50µA	800	-	-	V
Zero gate voltage drain current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μΑ
		VDS=0.8Max., Rating, VGS=0V, TC=125°C	-	-	200	μΑ
Static drain source on resistance (note)	RDS(ON)	VGS=10V, ID=5.0A	-	1.2	1.5	Ω
Forward transconductance (note)	gfs	V <sub>DS</sub> =15V, I <sub>D</sub> =5.0A	1.5	2.5	-	S
Input capacitance	Ciss		-	2460	-	pF
Output capacitance	Coss	VGS=0V, VDS=25V, f=1MHz	-	210	-	
Reverse transfer capacitance	Crss	1-110112	-	64	-	
Turn on delay time	td(on)	VDD=0.5BVDSS, ID=8.0A (MOSFET switching time are essentially independent of operating temperature)	-	-	90	
Rise time	tr		-	95	200	nS
Turn off delay time	td(off)		-	150	450	115
Fall time	tf		-	60	150	
Total gate charge (gate-source+gate-drain)	Qg	V <sub>GS</sub> =10V, I <sub>D</sub> =8.0A, V <sub>DS</sub> =0.5BV <sub>DSS</sub> (MOSFET switching time are essentially independent of	-	-	150	
Gate source charge	Qgs		-	20	-	nC
Gate drain (Miller) charge	Qgd	operating temperature)	-	70	-	

#### Note:

Pulse test: Pulse width  $\leq 300\mu$ S, duty cycle  $\leq 2\%$ S =  $\frac{1}{R}$ 

# **Electrical Characteristics (CONTROL part)**

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
UVLO SECTION					•	•
Start threshold voltage	VSTART	-	14	15	16	V
Stop threshold voltage	VSTOP	After turn on	9	10	11	V
OSCILLATOR SECTION					•	•
Initial accuracy	Fosc	KA1L0880B	45	50	55	kHz
		KA1M0880B	61	67	73	
Frequency change with temperature <sup>(2)</sup>	$\Delta F / \Delta T$	–25°C ≤ Ta ≤ +85°C	-	±5	±10	%
Maximum duty cycle	Dmax		74	77	80	%
FEEDBACK SECTION						
Feedback source current	IFB	Ta=25°C, $0V \le Vfb \le 3V$	0.7	0.9	1.1	mA
Shutdown Feedback voltage	VSD	-	6.9	7.5	8.1	V
Shutdown delay current	Idelay	Ta=25°C, 5V $\leq$ Vfb $\leq$ VsD	4.0	5.0	6.0	μΑ
SOFT START SECTION						
Soft Start Voltage	Vss	VFB =2V	4.7	5.0	5.3	V
Soft Start Current	ISS	Sync & S/S=GND	0.8	1.0	1.2	mA
REFERENCE SECTION						
Output voltage <sup>(1)</sup>	Vref	Ta=25°C	4.80	5.00	5.20	V
Temperature Stability <sup>(1)(2)</sup>	Vref/∆T	–25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C
CURRENT LIMIT (SELF-PROTECTION	I) SECTION					
Peak Current Limit	IOVER	Max. inductor current	4.40	5.00	5.60	A
PROTECTION SECTION						
Thermal shutdown temperature (Tj) <sup>(1)</sup>	TSD	-	140	160	-	°C
Over voltage protection voltage	Vovp	-	23	25	28	V
TOTAL DEVICE SECTION						
Start Up current	ISTART	V <sub>CC</sub> =14V	0.1	0.3	0.45	mA
Operating supply current (control part only)	IOP	Ta=25°C	6	12	18	mA
VCC zener voltage	Vz	ICC=20mA	30	32.5	35	V

Note:

1. These parameters, although guaranteed, are not 100% tested in production

2. These parameters, although guaranteed, are tested in EDS (wafer test) process

### **Typical Performance Characteristics**

(These characteristic graphs are normalized at Ta=25°C)

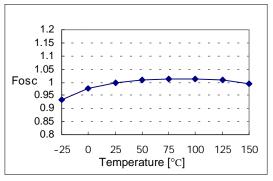


Figure 1. Operating Frequency

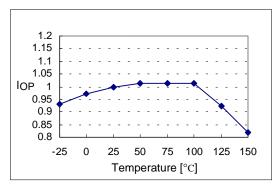


Figure 3. Operating Supply Current

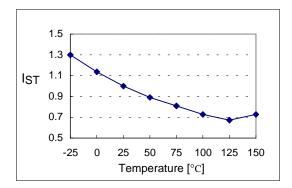


Figure 5. Start up Current

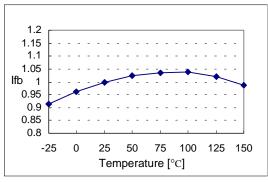


Figure 2. Feedback Source Current

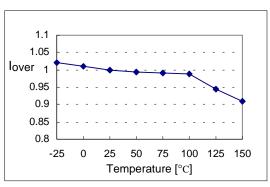


Figure 4. Peak Current Limit

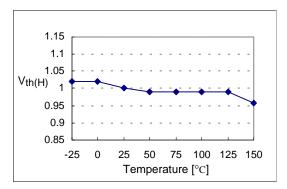


Figure 6. Start Threshold Voltage

#### Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at Ta=25°C)

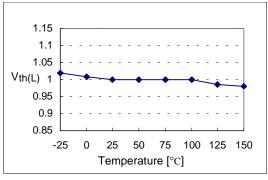


Figure 7. Stop Threshold Voltage

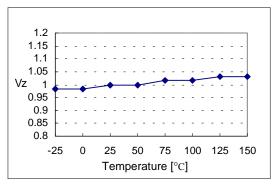


Figure 9. VCC Zener Voltage

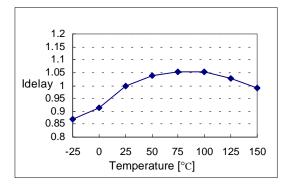


Figure 11. Shutdown Delay Current

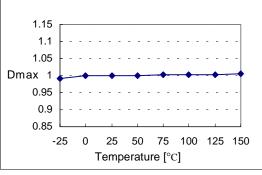


Figure 8. Maximum Duty Cycle

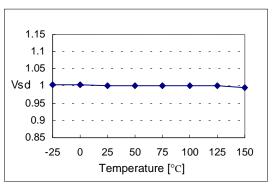


Figure 10. Shutdown Feedback Voltage

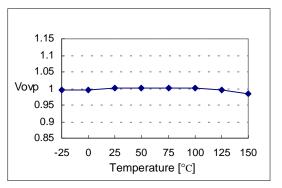


Figure 12. Over Voltage Protection

## Typical Performance Characteristics (Continued)

(These characteristic grahps are normalized at Ta=25°C)

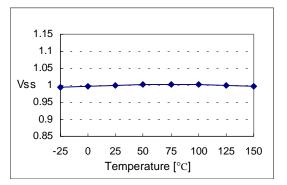


Figure 13. Soft Start Voltage

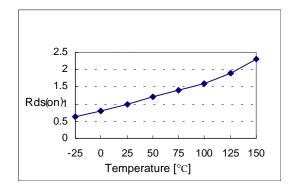
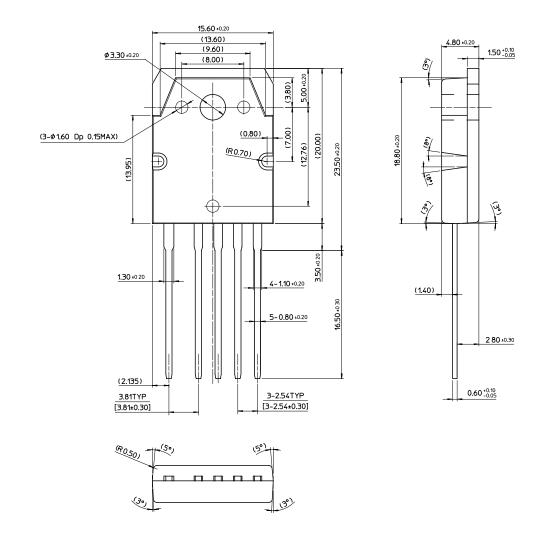


Figure 14. Static Drain Source on Resistance

## **Package Dimensions**

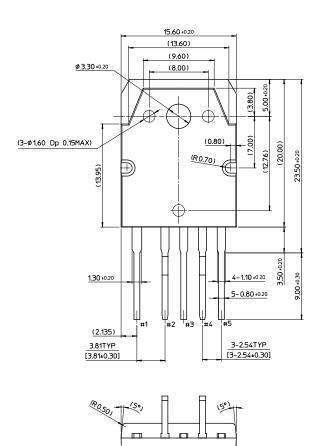




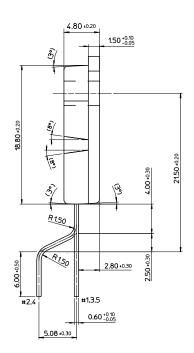
# Package Dimensions

# TO-3P-5L (Forming)

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#### **Ordering Information**

Product Number	Package	Rating	Fosc	
KA1L0880B-TU	TO-3P-5L	800V, 8A	50kHz	
KA1L0880B-YDTU	TO-3P-5L(Forming)	000V, 0A		
KA1M0880B-TU	TO-3P-5L	800V, 8A	67kHz	
KA1M0880B-YDTU	TO-3P-5L(Forming)	000V, 0A	07 KHZ	

TU : Non Forming Type YDTU : Forming type

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